

ESH1PB, ESH1PC & ESH1PD

New Product Vishay General Semiconductor

High Current Density Surface Mount Ultrafast Rectifiers



DO-220AA (SMP)

MAJOR RATINGS AND CHARACTERISTICS				
I _{F(AV)}	1 A			
V _{RRM}	100 V, 150 V, 200 V			
t _{rr}	25 ns			
V _F	0.90 V			
T _j max.	175 °C			

FEATURES

· Very low profile - typical height of 1.0 mm



- · Ideal for automated placement
- · Glass passivated chip junction
- Ultrafast recovery times for high frequency
- Low forward voltage drop, low power loss
- · Low thermal resistance
- Meets MSL level 1 per J-STD-020C, LF max peak of 260 °C
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

TYPICAL APPLICATIONS

For use in secondary rectification and freewheeling for ultrafast switching speeds of ac-to-ac and dc-to-dc converters in high temperature conditions for both consumer and automotive applications.

MECHANICAL DATA

Case: DO-220AA (SMP)

Epoxy meets UL-94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per

J-STD-002B and JESD22-B102D

E3 suffix for commercial grade, HE3 suffix for high

reliability grade (AEC Q101 qualified)

Polarity: Color band denotes cathode end

MAXIMUM RATINGS (T _A = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	ESH1PB	ESH1PC	ESH1PD	UNIT
Device marking code		PB	PC	PD	
Maximum repetitive peak reverse voltage	V_{RRM}	100	150	200	V
Maximum average forward rectified current (Fig. 1)	I _{F(AV)}	1.0			Α
Peak forward surge current 10 ms single half sine- wave superimposed on rated load	I _{FSM}	50			Α
Operating junction and storage temperature range	T _J , T _{STG}	- 55 to + 175			°C

ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Maximum instantaneous forward voltage ⁽¹⁾	at $I_F = 0.7 \text{ A}$, $T_j = 25 ^{\circ}\text{C}$ at $I_F = 1 \text{ A}$, $T_j = 25 ^{\circ}\text{C}$	V _F	0.86 0.90	V	
Maximum reverse current at rated $V_R^{(1)}$ voltage	$T_j = 25 ^{\circ}\text{C}$ $T_j = 125 ^{\circ}\text{C}$	I _R	1.0 25	μΑ	
Maximum reverse current	at V _R = 20 V, T _j = 150 °C	I _R	50	μΑ	

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ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Maximum reverse recovery time	at $I_F = 0.5 \text{ A}$, $I_R = 1 \text{ A}$, $I_{rr} = 0.25 \text{ A}$	t _{rr}	25	ns	
Typical reverse recovery time	at $I_F = 1.0$ A, $V_R = 30$ V di/dt = 50 A/ μ s, $I_{rr} = 10$ % I_{RM} $T_j = 25$ °C at $I_F = 1.0$ A, $V_R = 30$ V di/dt = 50 A/ μ s, $I_{rr} = 10$ % I_{RM} $T_j = 100$ °C	t _{rr}	25 35	ns	
Typical reverse recovery time	at $I_F = 1.0$ A, $V_R = 30$ V di/dt = 50 A/ μ s, $I_{rr} = 10$ % I_{RM} $T_j = 25$ °C at $I_F = 1.0$ A, $V_R = 30$ V di/dt = 50 A/ μ s, $I_{rr} = 10$ % I_{RM} $T_j = 100$ °C	Q _{rr}	10 15	nC	
Typical junction capacitance	at 4.0 V, 1 MHz	CJ	25	pF	

Note:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	ESH1PB	ESH1PC	ESH1PD	UNIT
Typical thermal resistance ⁽¹⁾	$egin{array}{c} {\sf R}_{ heta {\sf JA}} \ {\sf R}_{ heta {\sf JL}} \ {\sf R}_{ heta {\sf JC}} \end{array}$	105 15 20		°C/W	

Note:

(1) Thermal resistance from junction to ambient and junction to lead mounted on P.C.B. with 5.0 x 5.0 mm copper pad areas. $R_{\theta JL}$ is measured at the terminal of cathode band. $R_{\theta JC}$ is measured at the top centre of the body

ORDERING INFORMATION						
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
ESH1PB-E3/84A	0.024	84A	3000	7" Diameter Plastic Tape & Reel		
ESH1PB-E3/85A	0.024	85A	10000	13" Diameter Plastic Tape & Reel		

RATINGS AND CHARACTERISTICS CURVES

 $(T_A = 25 \, ^{\circ}C \text{ unless otherwise noted})$

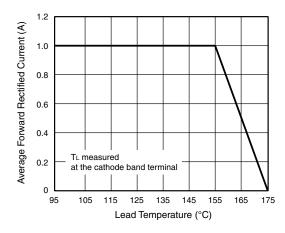


Figure 1. Forward Current Derating Curve

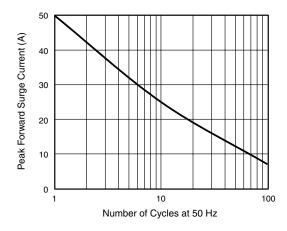


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current

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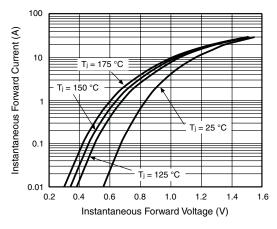


Figure 3. Typical Instantaneous Forward Characteristics

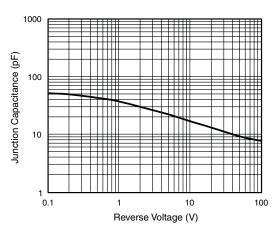


Figure 5. Typical Junction Capacitance

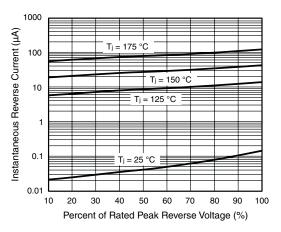


Figure 4. Typical Reverse Leakage Characteristics

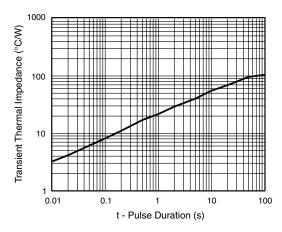
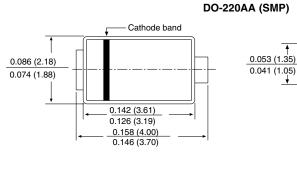
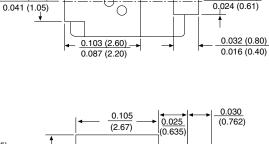


Figure 6. Typical Transient Thermal impedance

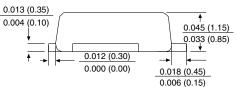
0.036 (0.91)

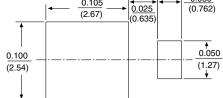
PACKAGE OUTLINE DIMENSIONS in inches (millimeters)





0.012 (0.30) REF





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